SERIAL NO. ATTY DOCKET NO. U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE Form PTO 1449 (Modified) 10/019,278 217218US2PCT DRADEMAR **APPLICANT** LIST OF REFERENCES CITED BY APPLICANT Marc DELAUNAY, et al. **GROUP** FILING DATE 1762 January 2, 2002 **U.S. PATENT DOCUMENTS FILING DATE** SUB **DOCUMENT EXAMINER CLASS** DATE NAME CLASS IF APPROPRIATE INITIAL NUMBER AA AB AC AD ΑE ΑF AG AH ΑI AJ AK AL AM AN FOREIGN PATENT DOCUMENTS **TRANSLATION DOCUMENT** DATE COUNTRY **NUMBER** YES AO AP AQ AR AS **AT** ΑU ΑV OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.) A.Y. Tcherepanov et al, Flat Panel Displays Based Upon Low-Voltage Carbon Field Emitters, 7th International Vacuum ΑW Microelectronics Conference, July 1994, vol. 50, pgs. 205-208. D. Hong et al., Field Emission From P-Type Polycrystalline Diamond Films, 7th International Vacuum Microelectronics AX Conference, Number 271, April 1994, pgs. 96-99. M. Delaunay et al. Electron Cyclotron Resonance Plasma Ion Source for Material Depositions, Review of Scientific Instruments, vol. 69, Number 6, June 1998, pgs. 2320-2324. AY Seilchiro Matsumoto, Chemical Vapour Deposition of Diamond in RF Glow Discharge, Journal of Materials Science Letters 4, 1985, pgs. 600-602. Additional References sheet(s) attached Date Considered 4/14/10 Examiner \*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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